

# EIC1011-8

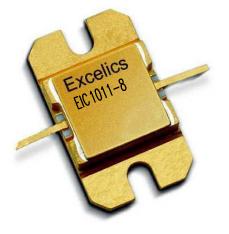
## 10.70-11.70 GHz 8-Watt Internally-Matched Power FET

#### **FEATURES**

- 10.70 11.70 GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +39.0 dBm Output Power at 1dB Compression
- 6 dB Power Gain at 1dB Compression
- 30% Power Added Efficiency
- -46 dBc IM3 at Po = 28.5 dBm SCL
- Hermetic Metal Flange Package
- 100% Tested for DC, RF, and  $R_{TH}$

#### DESCRIPTION

The EIC1011-8 is a high power, highly linear, single stage MFET amplifier in a flange mount package. This amplifier features Excelics' unique MESFET transistor technology.





Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS <sup>1</sup>	MIN	TYP	MAX	UNITS
P <sub>1dB</sub>	Output Power at 1dB Compression f = 10.7-11.7GHz V <sub>DS</sub> = 10 V, $I_{DSQ} \approx 2200$ mA	38.5	39.0		dBm
G <sub>1dB</sub>	Gain at 1dB Compression $f = 10.7-11.7GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 2200 \text{mA}$	5.0	6.0		dB
∆G	Gain Flatnessf = 10.7-11.7GHz $V_{DS}$ = 10 V, $I_{DSQ} \approx 2200$ mA			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS}$ = 10 V, $I_{DSQ} \approx 2200$ mAf = 10.7-11.7GHz		30		%
Id <sub>1dB</sub>	Drain Current at 1dB Compression f = 10.7-11.7GHz		2200	2600	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f$ = 10 MHz 2-Tone Test; Pout = 28.5 dBm S.C.L <sup>2</sup> $V_{DS}$ = 10 V, $I_{DSQ} \approx 65\%$ IDSSf = 11.70 GHz	-43	-46		dBc
I <sub>DSS</sub>	Saturated Drain Current $V_{DS} = 3 V, V_{GS} = 0 V$		4000	4500	mA
V <sub>P</sub>	Pinch-off Voltage $V_{DS}$ = 3 V, $I_{DS}$ = 40 mA		-2.5	-4.0	V
R <sub>TH</sub>	Thermal Resistance <sup>3</sup>		3.5	4.0	°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25°C)

Notes:

1. Tested with 100 Ohm gate resistor.

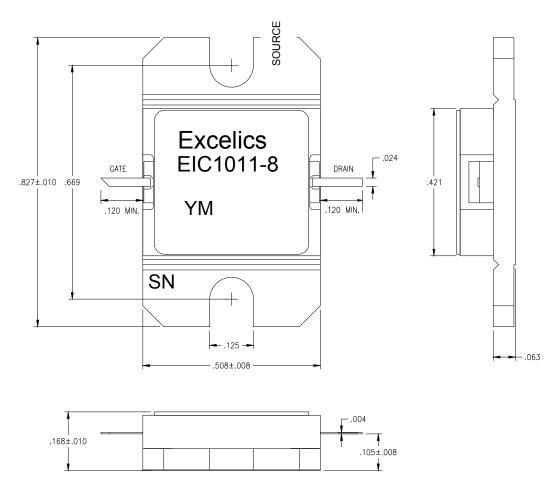
2. S.C.L. = Single Carrier Level.

3. Overall Rth depends on case mounting.



### PACKAGE OUTLINE

Dimensions in inches, Tolerance  $\pm$  .005 unless otherwise specified



#### **ORDERING INFORMATION**

Part Number	Grade <sup>1</sup>	f <sub>Test</sub> (GHz)	P <sub>1dB</sub> (min)	$IM_3$ (min) <sup>2</sup>
EIC1011-8	Industrial	10.70-11.70 GHz	38.5	-43

Notes: 1. Contact factory for military and hi-rel grades.

2. Exact test conditions are specified in "Electrical Characteristics" table.